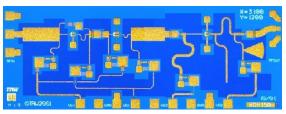




Product Datasheet Revision: April 2015



X=3100 μm Y=1200 μm

## **Applications**

- Short Haul / High Capacity Links
- Sensors
- Radar

#### **Features**

X2 Active Multiplier

Input frequency: 46 to 48 GHz

Output frequency: 92 to 96 GHz

Conversion Gain: 3 dB (typ.)

♦ Conversion Gain @ ~Pinchoff: 5 dB

(typ.)

♦ RF Input Power: -5 dB (typ.)

♦ Die Size: < 3.8 sq. mm</p>

# **Product Description**

The XDH150 is a monolithic HEMT multiplier designed for use in commercial digital radios and wireless LANs. To ensure rugged and reliable operation, HEMT devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression, and thermosonic wire bonding assembly techniques.

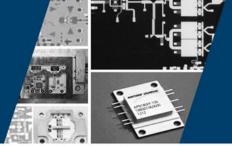
## **Performance Characteristics (T<sub>OP</sub> = 25°C)**

Specification	Min	Тур	Max	Unit
Input Frequency	46		48	GHz
Output Frequency	92		96	GHz
Input Power		-5		dBm
Output Power	-4	-2		dBm
Conversion Gain	1	3		dB
Vd1		4		V
ld1		80		mA
Vd2		4		V
ld2		20		mA
Vg1		0		V
Vg2		-0.1		V
Conversion Gain @		5		dB
~Pinchoff				
ld2 @ ~Pinchoff		0.5		mA

### Absolute Maximum Ratings (Top = 25°C)

Parameter	Min	Max	Unit
Vd1		5.5	V
ld1		90	mΑ
Vd2		5.5	V
ld2		20	mA
Vg1	-1	+0.3	V
Vg2	-1	+0.3	V
Input Drive Level		0	dBm
Assy. Temperature		300	°C
(60 seconds)			

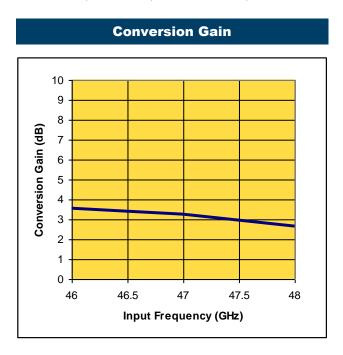
Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).

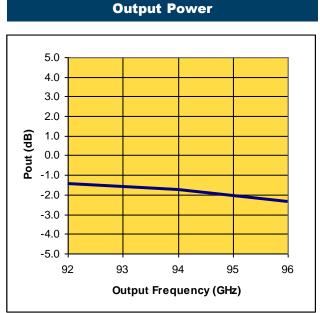




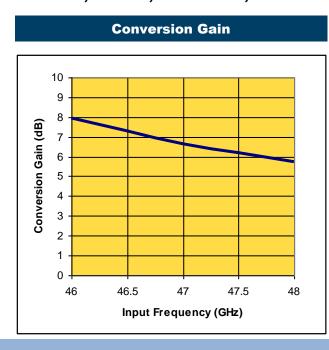
Product Datasheet Revision: April 2015

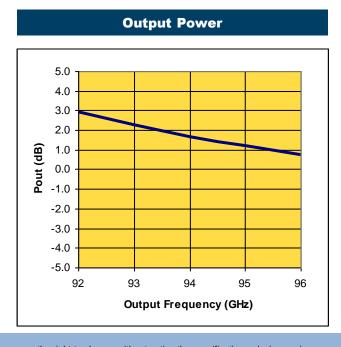
On-Wafer Measured Performance Characteristics ( $T_{OP} = 25^{\circ}C$ ) Pin = -5 dBm, Vd = 4V, Id1 = 80 mA, Id2 = 20 mA (Screen Specification Conditions)



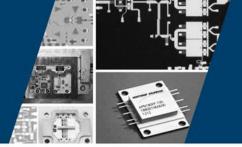


On-Wafer Measured Performance Characteristics ( $T_{OP} = 25$ °C) Pin = -5 dBm, Vd = 4V, Id1 = 80 mA, Id2 = 0.5 mA





Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).





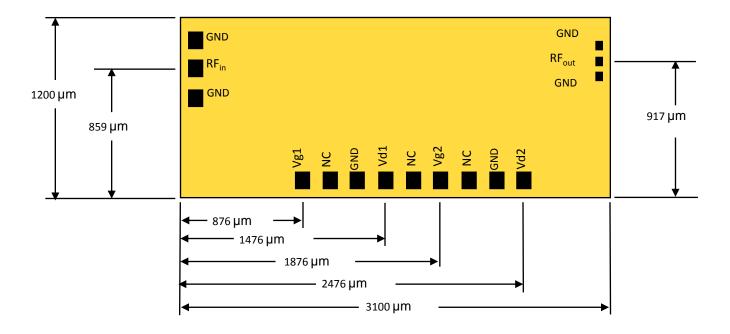
Product Datasheet Revision: April 2015

### Die Size and Bond Pad Locations (Not to Scale)

X Dimension:  $3100 \pm 25 \mu m$  Y Dimension:  $1200 \pm 25 \mu m$ 

DC & Input RF Bond Pad Dimension: 101 x 101  $\mu$ m  $\pm$  0.5  $\mu$ m Output RF Bond Pad Dimension: 51 x 51  $\mu$ m  $\pm$  0.5  $\mu$ m

Chip Thickness =  $101 \pm 5 \mu m$ 







**Product Datasheet** 

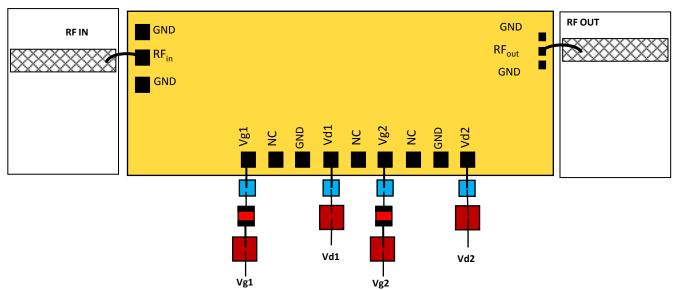
## **Suggested Bonding Arrangement**

Revision: April 2015

= 0.1uF, 15V (Shunt)

= 10 Ohms, 30V (Series)

= 100 pF, 15V (Shunt)



#### **Recommended Assembly Notes**

- 1. Bypass caps should be 100 pF (approximately) ceramic (single-layer) placed no farther than 30 mils from the amplifier.
- 2. Input bond pad & dc bias pads dimensions are 0.1mm x 0.1mm (4mil x 4mil).
- 3. Output bond pad dimension is 0.05mm x 0.05mm (2mil x 2mil).
- 4. Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbon on input bond pads and <6 mil (long) by 1.5 by 0.5 mil ribbon on output bond pads

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).